




NPN EPITAXIAL SILICON TRANSISTORS

WMBTA92

High Voltage Transistor			SOT—23			
<ul style="list-style-type: none">* Die Size 0.6X0.6mm* Power Dissipation: 225mW* Collector Current : Max 500mA* Bonding Pad Size Emittoe 100*100mkm base 100*100mkm					<div>1. BASE</div> <div>2. EMITTER</div> <div>3. COLLECTOR</div>	
GUARANTEED PROBED CHARACTERISTICS (T_A=25°C)						
Characteristic	Symbol	Test Conditions	Limits			Units
			Min	Typ	Max	
Collector-emitter Breakdown Voltage	V _{CEO}	I _C =1.0mA	300	-	-	V
Collector-Base Breakdown Voltage	V _{CBO}	I _C =100uA	300	-	-	V
Emitter-Base Breakdown Voltage	V _{EBO}	I _E =10uA	5.0	-	-	V
Collector Cut-off Current	I _{CBO}	V _{CB} =260V	-	-	100	nA
Emitter Cut-off Current	I _{EBO}	V _{EB} =6V	-	-	100	nA
DC Current Gain	h _{FE}	V _{CE} =10V, I _C =1mA V _{CE} =10V, I _C =10mA V _{CE} =10V, I _C =30mA	30 40 40	-	-	
Base-Emitter Saturation Voltage	V _{BEsat}	I _C =20mA, I _B =2mA	-	-	0.90	V
Collector-Emitter Saturation Voltage	V _{CEsat}	I _C =20mA, I _B =2mA	-	-	0.35	V
Transition Frequency	f _r	V _{CE} =20V, I _C =10mA,f=10MHz	50	-	-	MHz
Collector-Base Capacitance	C _{cb}	V _{CB} =20V, f=1MHz	-	-	6.0	pF
NOTES: Due to probe testing limitations, only the DC parameters are tested.						